

PATENT APPLICATION
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q78084

Hiromitsu SAKAI, et al.

Appln. No.: 10/575,625

Group Art Unit: 2811

Confirmation No.: 4644

Examiner: Shouxiang HU

Filed: April 13, 2006

For: GROUP-III NITRIDE SEMICONDUCTOR DEVICE

RESPONSE UNDER 37 C.F.R. § 1.111

MAIL STOP RESPONSE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated May 13, 2010, please amend the above-identified application as follows on the accompanying pages.

REMARKS

Review and reconsideration on the merits are requested.

Claims 1-4, 6-14, and 16 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Shibata (U.S. Patent Application Publication No. 2002/0155682) in view of Chang (U.S. Patent No. 6,504,183).

In the Office Action, Shibata was cited as disclosing a Group III nitride semiconductor element including AlN single crystal layer 1 provided on a sapphire (Al_2O_3) substrate, an island-shaped second nitride semiconductor layer (2-1, 2-2, 2-3 and 2-4) composed of $\text{Al}_{x1}\text{Ga}_{1-x1}\text{N}$, where $x1 = 0.1$ provided on the first nitride semiconductor layer; and a third nitride